

**CMFSH-3i**  
**SURFACE MOUNT  
DUAL, ISOLATED  
SILICON SCHOTTKY DIODES**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMFSH-3i consists of two electrically isolated silicon Schottky diodes packaged in an epoxy molded SOT-143 surface mount case. This device is designed for fast switching applications requiring a low forward voltage drop.



**MARKING CODE: C3I**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Peak Repetitive Reverse Voltage  
Continuous Forward Current  
Peak Repetitive Forward Current  
Peak Forward Surge Current,  $t_p=10\text{ms}$   
Power Dissipation  
Operating and Storage Junction Temperature  
Thermal Resistance

**SYMBOL**

$V_{RRM}$  30  
 $I_F$  100  
 $I_{FRM}$  200  
 $I_{FSM}$  750  
 $P_D$  350  
 $T_J, T_{stg}$  -65 to +150  
 $\theta_{JA}$  357

**UNITS**

V  
mA  
mA  
mA  
mW  
 $^\circ\text{C}$   
 $^\circ\text{C/W}$

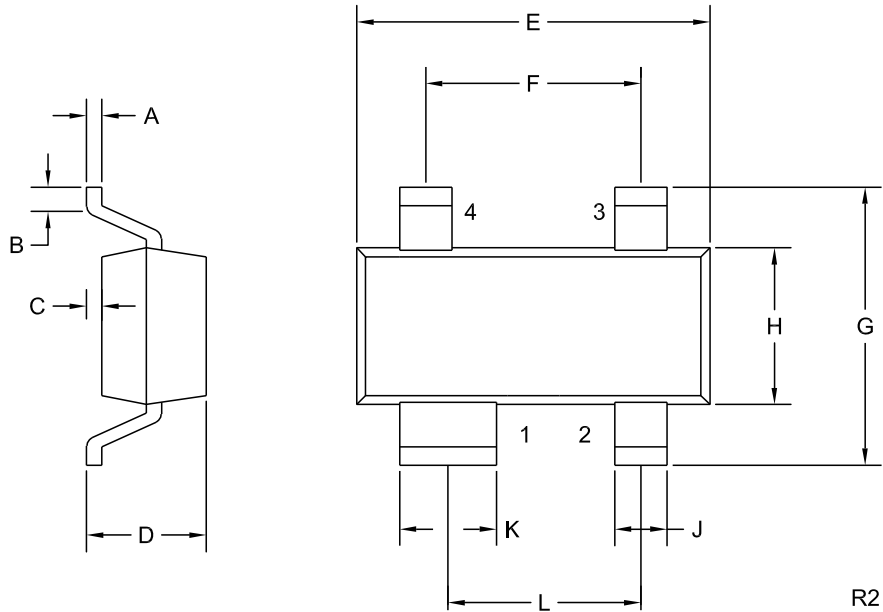
**ELECTRICAL CHARACTERISTICS PER DIODE:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_R$	$V_R=25\text{V}$		90	500	nA
$I_R$	$V_R=25\text{V}, T_A=100^\circ\text{C}$		25	100	$\mu\text{A}$
$BV_R$	$I_R=100\mu\text{A}$	30			V
$V_F$	$I_F=2.0\text{mA}$		0.29	0.33	V
$V_F$	$I_F=15\text{mA}$		0.40	0.45	V
$V_F$	$I_F=100\text{mA}$		0.74	1.00	V
$C_T$	$V_R=1.0\text{V}, f=1.0\text{MHz}$		7.0		pF
$t_{rr}$	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

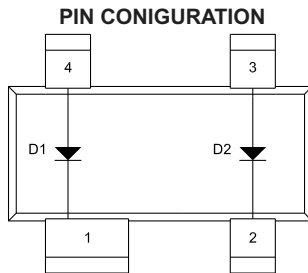
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**SOT-143 CASE - MECHANICAL OUTLINE**



R2



- LEAD CODE:**  
 1) Cathode D1  
 2) Cathode D2  
 3) Anode D2  
 4) Anode D1

**MARKING CODE: C3I**

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.006	0.08	0.15
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	-	0.045	-	1.14
E	0.110	0.120	2.79	3.04
F	0.075		1.90	
G	-	0.098	-	2.50
H	0.047	0.055	1.19	1.40
J	0.014	0.020	0.36	0.50
K	0.030	0.037	0.76	0.93
L	0.067		1.70	

SOT-143 (REV: R2)

R5 (13-August 2010)